

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A photoelectric transducer comprising a first pin junction part including:
  - a first p-layer;
  - a first n-layer disposed so as to oppose the first p-layer; and
  - a first i-layer, disposed between the first p-layer and first n-layer, containing an iron atom, a silicon atom bonded to the iron atom, and a hydrogen atom,  
wherein a composition ratio between the iron atom and silicon atom in the first i-layer is in a range from 1:1.7 to 1:3.5.
2. (Original) A photoelectric transducer according to claim 1, wherein the first i-layer is formed by at least partly bonding the hydrogen atom to the silicon atom or iron atom.
3. (Previously Presented) A photoelectric transducer according to claim 1, wherein the first i-layer is mainly amorphous.
4. (Previously Presented) A photoelectric transducer according to claim 1, wherein the first i-layer has a hydrogen atom content of 1 to 25 atom %.
5. (Previously Presented) A photoelectric transducer according to claim 1, wherein the first pin junction part further comprises a second i-layer disposed between the first p-layer and first n-layer and constituted by a mainly amorphous silicon film.
6. (Previously Presented) A photoelectric transducer according to claim 1, further comprising a second pin junction part, disposed in series with the first pin junction part, including:
  - a second p-layer;
  - a second n-layer disposed so as to oppose the second p-layer; and

a third i-layer disposed between the second p-layer and second n-layer and made of an amorphous silicon film.

7. (Currently Amended) A photoelectric transducer apparatus comprising:  
a substrate;  
a first electrode layer disposed on one side of the substrate;  
a second electrode layer disposed so as to oppose the first electrode layer; and  
a first pin junction part including a first n-layer formed on the first electrode layer, a first p-layer formed on one side of the second electrode layer so as to oppose the first n-layer, and a first i-layer, disposed between the first p-layer and first n-layer, containing an iron atom, a silicon atom bonded to the iron atom, and a hydrogen atom,  
wherein a composition ratio between the iron atom and silicon atom in the first i-layer is in a range from 1:1.7 to 1:3.5.

8. (Currently Amended) An iron silicide film for constructing an i-layer in a pin junction;  
the iron silicide film containing an iron atom, a silicon atom bonded to the iron atom, and a hydrogen atom while being mainly amorphous,  
wherein a composition ratio between the iron atom and silicon atom is in a range from 1:1.7 to 1:3.5.

9. (Previously Presented) A photoelectric transducer according to claim 2, wherein the first i-layer is mainly amorphous.

10. (Previously Presented) A photoelectric transducer according to claim 2, wherein the first i-layer has a hydrogen atom content of 1 to 25 atom %.

11. (Previously Presented) A photoelectric transducer according to claim 3, wherein the first i-layer has a hydrogen atom content of 1 to 25 atom %.

12. (Previously Presented) A photoelectric transducer according to claim 2, wherein the first pin junction part further comprises a second i-layer disposed between the first p-layer and first n-layer and constituted by a mainly amorphous silicon film.

13. (Previously Presented) A photoelectric transducer according to claim 3, wherein the first pin junction part further comprises a second i-layer disposed between the first p-layer and first n-layer and constituted by a mainly amorphous silicon film.

14. (Previously Presented) A photoelectric transducer according to claim 4, wherein the first pin junction part further comprises a second i-layer disposed between the first p-layer and first n-layer and constituted by a mainly amorphous silicon film.

15. (Previously Presented) A photoelectric transducer according to claim 2, further comprising a second pin junction part, disposed in series with the first pin junction part, including:

a second p-layer;

a second n-layer disposed so as to oppose the second p-layer; and

a third i-layer disposed between the second p-layer and second n-layer and

made of an amorphous silicon film.

16. (Previously Presented) A photoelectric transducer according to claim 3, further comprising a second pin junction part, disposed in series with the first pin junction part, including:

a second p-layer;

a second n-layer disposed so as to oppose the second p-layer; and

a third i-layer disposed between the second p-layer and second n-layer and

made of an amorphous silicon film.

17. (Previously Presented) A photoelectric transducer according to claim 4, further comprising a second pin junction part, disposed in series with the first pin junction part, including:

a second p-layer;

a second n-layer disposed so as to oppose the second p-layer; and

a third i-layer disposed between the second p-layer and second n-layer and

made of an amorphous silicon film.

18. (New) A photoelectric transducer according to claim 1, wherein the composition ratio between the iron atom and silicon atom in the first i-layer is substantially 1:2.

19. (New) A photoelectric transducer according to claim 7, wherein the composition ratio between the iron atom and silicon atom in the first i-layer is substantially 1:2.

20. (New) An iron silicide film according to claim 8, wherein the composition ratio between the iron atom and silicon atom in the first i-layer is substantially 1:2.